#### Memory in SystemVerilog

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**Implementing Memory** 

#### Memory = Storage Element Array + Addressing

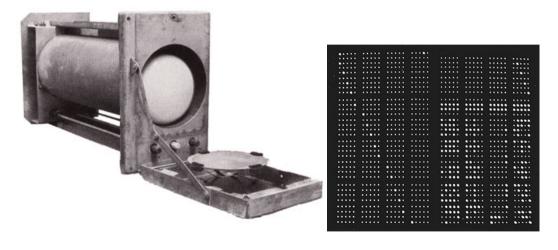
#### Bits are expensive

They should dumb, cheap, small, and tighly packed

#### Bits are numerous

Can't just connect a long wire to each one

#### Williams Tube



CRT-based random access memory, 1946. Used on the Manchester Mark I. 2048 bits.

### Mercury acoustic delay line



Used in the EDASC, 1947.

 $32 \times 17$  bits

#### **Selectron Tube**



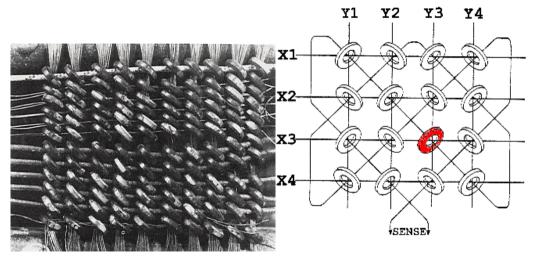
RCA, 1948.

 $2 \times 128 \text{ bits}$ 

Four-dimensional addressing

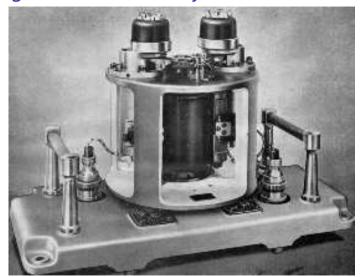
A four-input AND gate at each bit for selection

#### **Magnetic Core**



IBM, 1952.

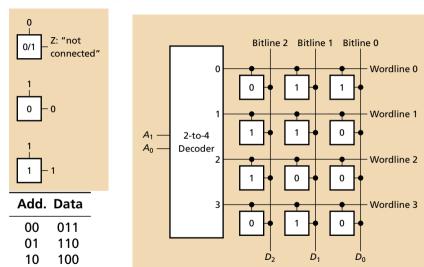
#### **Magnetic Drum Memory**

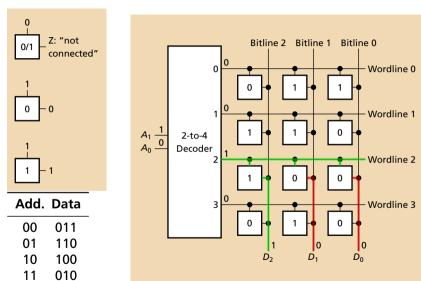


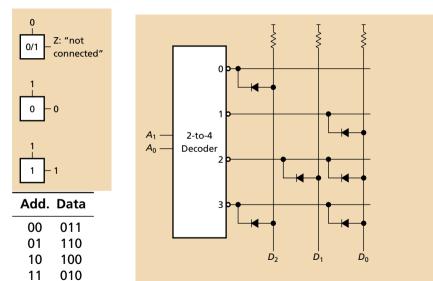
1950s & 60s. Secondary storage.

# **Modern Memory Choices**

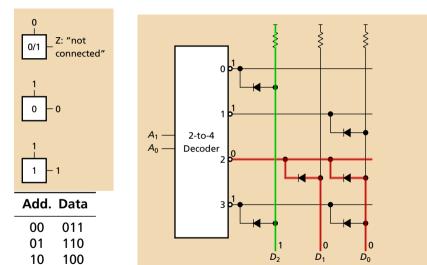
	Family	Programmed	Persistence
	Mask ROM	at fabrication	$\infty$
	PROM	once	$\infty$
	EPROM	1000s, UV erase	10 years
	FLASH	1000s, block erase	10 years
	EEPROM	1000s, byte erase	10 years
	NVRAM	$\infty$	5 years
	SRAM	$\infty$	while powered
	DRAM	$\infty$	64 ms



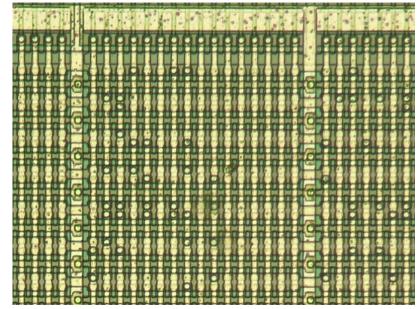




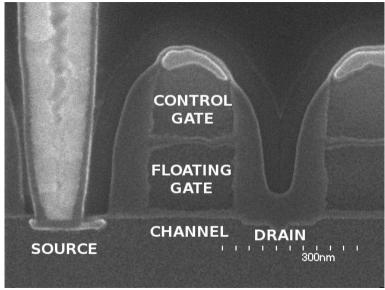
010



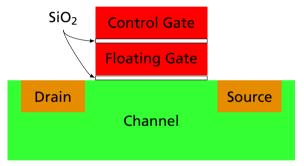
#### Mask ROM Die Photo



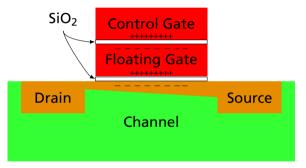
#### A Floating Gate MOSFET



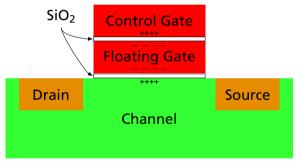
Cross section of a NOR FLASH transistor. Kawai et al., ISSCC 2008 (Renesas)



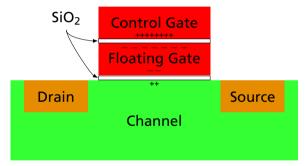
Floating gate uncharged; Control gate at 0V: Off



Floating gate uncharged; Control gate positive: On

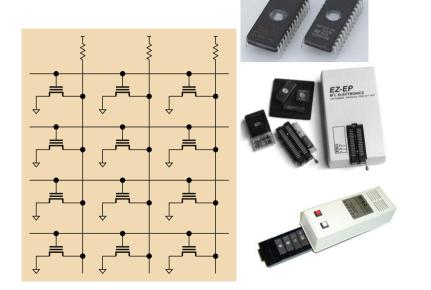


Floating gate negative; Control gate at 0V: Off

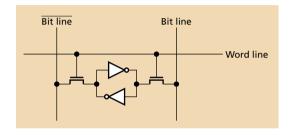


Floating gate negative; Control gate positive: Off

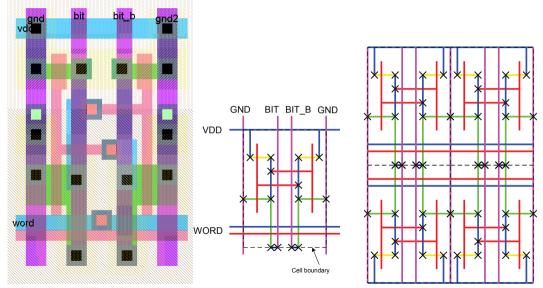
### **EPROMs and FLASH use Floating-Gate MOSFETs**



#### Static Random-Access Memory Cell

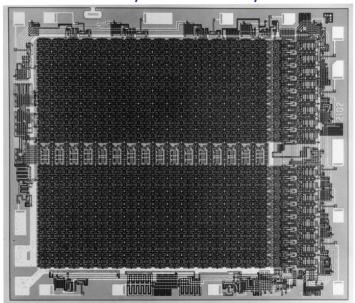


#### Layout of a 6T SRAM Cell

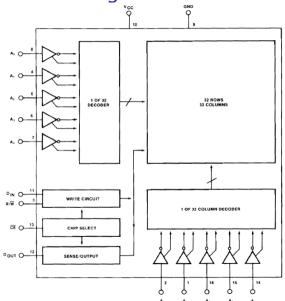


Weste and Harris. Introduction to CMOS VLSI Design. Addison-Wesley, 2010.

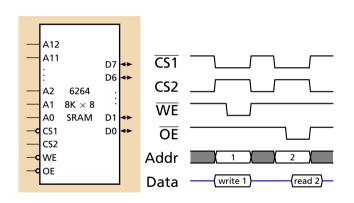
#### Intel's 2102 SRAM, 1024 × 1 bit, 1972



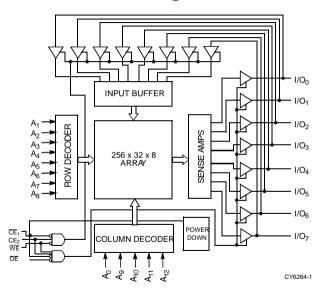
### 2102 Block Diagram



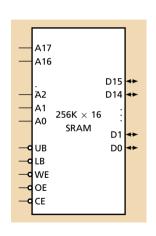
#### **SRAM Timing**

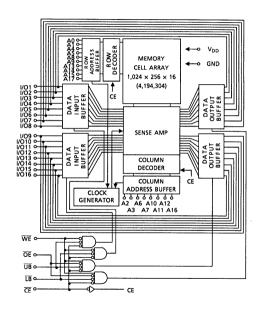


#### 6264 SRAM Block Diagram

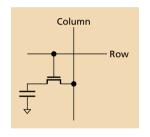


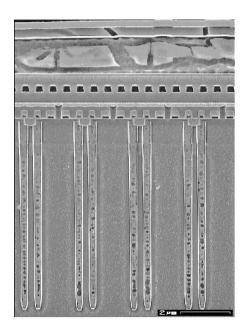
#### Toshiba TC55V16256J 256K × 16



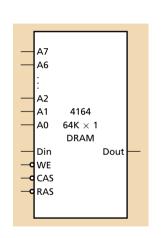


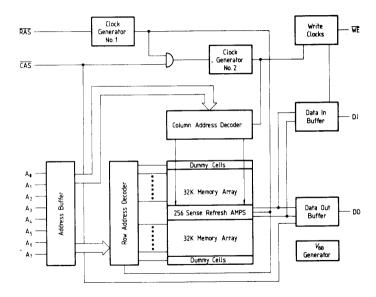
## Dynamic RAM Cell



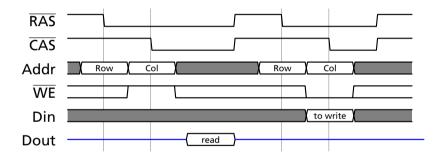


#### Ancient (c. 1982) DRAM: 4164 64K $\times$ 1

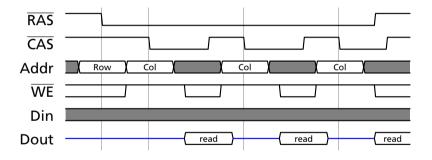




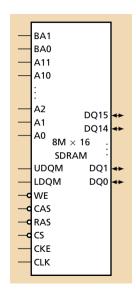
#### Basic DRAM read and write cycles

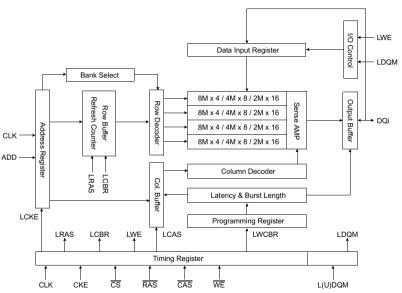


#### Page Mode DRAM read cycle



#### Samsung 8M × 16 SDRAM



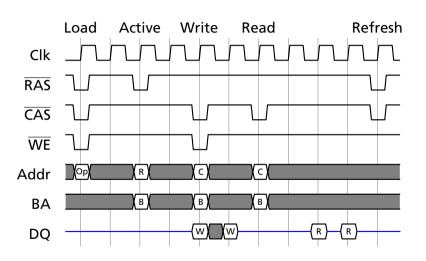


#### **SDRAM: Control Signals**

RAS	CAS	WE	Action
1	1	1	NOP
0	0	0	Load mode register
0	1	1	Active (select row)
1	0	1	Read (select column, start burst)
1	0	0	Write (select column, start burst)
1	1	0	Terminate Burst
0	1	0	Precharge (deselect row)
0	0	1	Auto Refresh

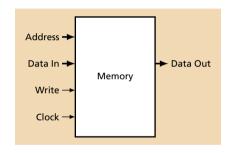
Mode register: selects 1/2/4/8-word bursts, CAS latency, burst on write

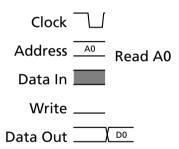
#### SDRAM: Timing with 2-word bursts



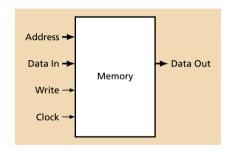
Using Memory in SystemVerilog

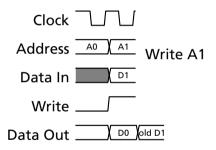
#### Synchronous SRAM



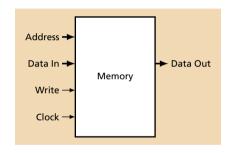


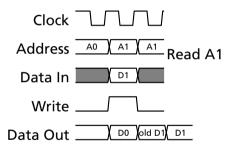
## Synchronous SRAM





## Synchronous SRAM





## Memory: A Fundamental Bottleneck



Plenty of bits, but

You can only see a small window each clock cycle

Using memory = scheduling memory accesses

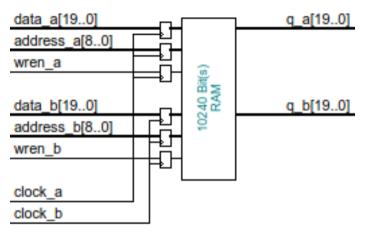
Software hides this from you: sequential programs naturally schedule accesses

In hardware, you must schedule memory accesses

## Modeling Synchronous Memory in SystemVerilog

```
Write enable
module memorv(
  input logic
                       clk
                                             4-bit address
  input logic
                       write
  input logic [3:0] address
                                            8-bit input bus
  input logic [7:0] data_in__.
  output logic [7:0] data_out);
                                            8-bit output bus
  logic [7:0] mem [15:0];
                                     The memory array: 16 8-bit bytes
  always_ff @(posedge clk)
                                        Clocked
  begin
    if (write)
      mem[address] <= data in:
                                        Write to array when asked
    data_out <= mem[address];</pre>
  end
endmodule
                                    Always read (old) value from array
```

## M10K Blocks in the Cyclone V



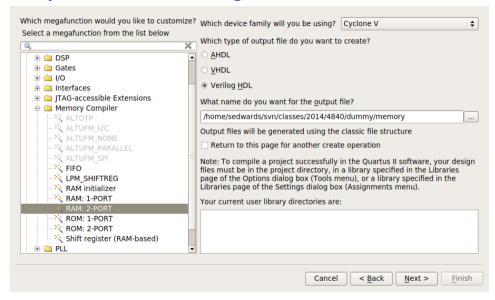
10 kilobits per block

Dual ported: two addresses, write enable signals

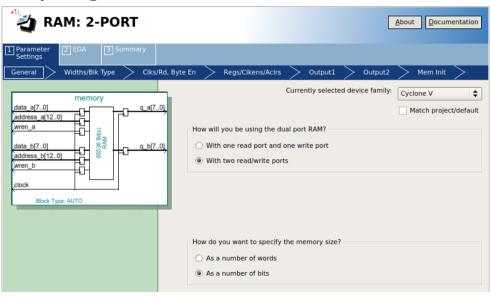
Data busses can be 1-20 bits wide

Our Cyclone 5CSEMA5 has 397 = 496 KB

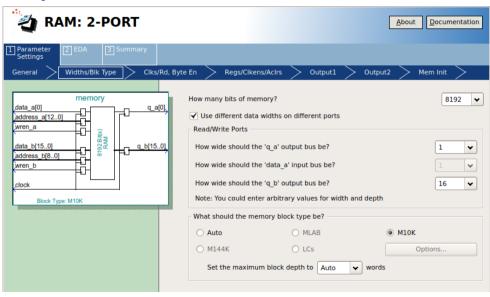
# Memory in Quartus: the Megafunction Wizard



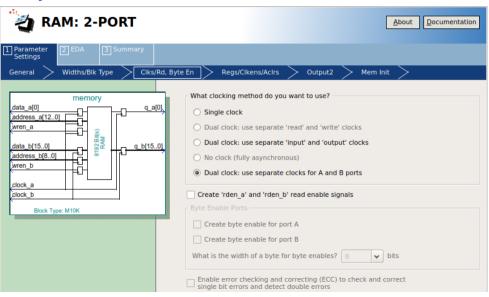
#### Memory: Single- or Dual-Ported



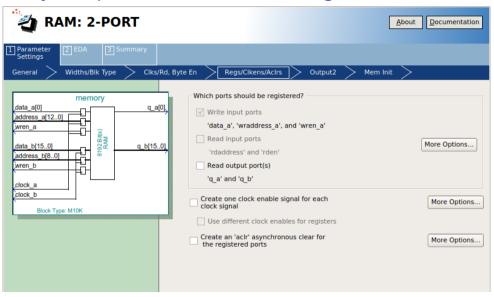
#### **Memory: Select Port Widths**



#### Memory: One or Two Clocks



#### Memory: Output Ports Need Not Be Registered



# Memory: Wizard-Generated Verilog Module

This generates the following SystemVerilog module:

```
module memory ( // Port A:
input logic [12:0] address_a, // 8192 1-bit words
input logic clock_a,
input logic [0:0] data_a,
input logic [0:0] q_a,

input logic [8:0] address_b, // 512 16-bit words
input logic clock_b,
input logic [15:0] data_b,
input logic [15:0] q_b);
```

Instantiate like any module; Quartus treats specially

# Two Ways to Ask for Memory

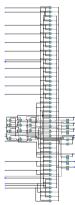
- 1. Use the Megafunction Wizard
  - + Warns you in advance about resource usage
  - Awkward to change
- 2. Let Quartus infer memory from your code
  - + Better integrated with your code
  - Easy to inadvertantly ask for garbage

```
module twoport(
  input logic clk.
  input logic [8:0] aa, ab,
  input logic [19:0] da, db,
  input logic wa, wb,
 output logic [19:0] qa, qb);
logic [19:0] mem [511:0]:
always_ff @(posedge clk) begin
 if (wa) mem[aa] <= da;
 qa \ll mem[aa];
 if (wb) mem[ab] <= db:</pre>
 qb <= mem[ab]:
end
endmodule
```

Failure: Exploded!

Synthesized to an 854-page schematic with 10280 registers (no M10K blocks)

Page 1 looked like this:



```
module twoport2(
  input logic clk.
  input logic [8:0] aa, ab,
  input logic [19:0] da. db.
  input logic wa, wb.
  output logic [19:0] ga. qb):
logic [19:0] mem [511:0];
always_ff @(posedge clk) begin
  if (wa) mem[aa] <= da:</pre>
  qa <= mem[aa]:
end
always_ff @(posedge clk) begin
  if (wb) mem[ab] <= db:</pre>
  qb <= mem[ab]:</pre>
end
endmodule
```

**Failure** 

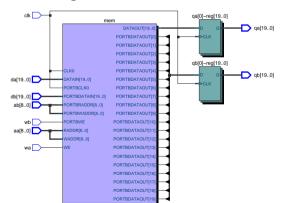
Still didn't work:

RAM logic "mem" is uninferred due to unsupported read-during-write behavior

```
module twoport3(
  input logic clk.
  input logic [8:0] aa, ab,
  input logic [19:0] da. db.
  input logic wa, wb.
  output logic [19:0] ga. qb):
logic [19:0] mem [511:0];
always_ff @(posedge clk) begin
  if (wa) begin
     mem[aa] <= da:
     aa <= da:</pre>
  end else qa <= mem[aa];</pre>
end
always_ff @(posedge clk) begin
  if (wb) begin
     mem[ab] \le db:
     ab \le db:
  end else ab <= mem[ab]:</pre>
end
endmodule
```

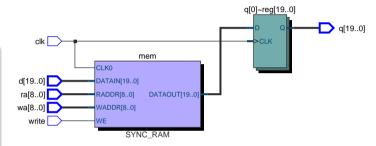
#### Finally!

Took this structure from a template: Edit→Insert Template→Verilog HDL→Full Designs→RAMs and ROMs→True Dual-Port RAM (single clock)



```
module twoport4(
  input logic clk.
  input logic [8:0] ra, wa,
  input logic write,
  input logic [19:0] d.
  output logic [19:0] q);
logic [19:0] mem [511:0];
always_ff @(posedge clk) begin
  if (write) mem[wa] <= d;</pre>
  a <= mem[ra]:</pre>
end
endmodule
```

Also works: separate read and write addresses



#### Conclusion:

Inference is fine for single port or one read and one write port.

Use the Megafunction Wizard for anything else.